

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-8. (Canceled)

9. (Currently amended) A nitride based semiconductor light-emitting device comprising:

a substrate;

a first conductive type nitride based semiconductor layer formed on the substrate;

an active layer with a p-n junction formed on said first conductive type nitride based semiconductor layer, said active layer being made of a nitride based semiconductor layer having the p-n junction;

a second conductive type nitride based semiconductor layer formed on said active layer, said second conductive type nitride based semiconductor layer being provided with protrusions, wherein having fine recesses are formed on a surface side and top surfaces of the protrusions;

a first ohmic electrode formed on the surface of said second conductive type nitride semiconductor layer; and

a second ohmic electrode formed on said first conductive type nitride based semiconductor layer.

10. (Currently amended) A nitride based semiconductor light-emitting device comprising:

a substrate;

a first conductive type nitride based semiconductor layer formed on the substrate;

an active layer with a p-n junction formed on said first conductive type nitride based semiconductor layer, said active layer being made of a nitride based semiconductor layer having the p-n junction;

a second conductive type nitride based semiconductor layer formed on said active layer, said second conductive type nitride based semiconductor layer being provided with protrusions whose surface ~~includes~~ surfaces include regions out of stoichiometric compositions;

a first ohmic electrode formed on the surface of said second conductive type nitride based semiconductor layer; and

a second ohmic electrode formed on said first conductive type nitride based semiconductor layer.

11. (Canceled)

12. (Currently amended) A nitride based semiconductor light-emitting device, comprising:

a substrate;

a first conductive type nitride based semiconductor layer formed on the substrate;

an active layer with a p-n junction formed on said first conductive type nitride based semiconductor layer, said active layer being made of a nitride based semiconductor layer having the p-n junction;

a second conductive type nitride based semiconductor layer formed on said active layer, said second conductive type nitride based semiconductor layer being provided with at least two sizes of protrusions formed on a surface of the second conductive type nitride based semiconductor layer, ~~said protrusions being provided with~~ wherein fine recesses are formed on a surface side and top surfaces of the protrusions;

a first ohmic electrode formed on the surface of said second conductive type nitride based semiconductor layer; and

a second ohmic electrode formed on said first conductive type nitride based semiconductor layer.

13. (Previously presented) A nitride based semiconductor light-emitting device according to Claim 9, wherein said protrusions have small and large ones.

14. (Previously presented) A nitride based semiconductor light-emitting device according to Claim 10, wherein said protrusions have small and large ones.

15-16. (Canceled)

17. (Previously presented) A nitride based semiconductor light-emitting device according to Claim 14 wherein said large protrusions are higher in height than the small protrusions.

18. (Previously presented) A nitride based semiconductor light-emitting device according to Claim 12, wherein said protrusions have small and large ones and said large protrusions are wider in width than the small protrusions.

19. (Previously presented) A nitride based semiconductor light-emitting device according to Claim 13, wherein said large protrusions are wider in width than the small protrusions.

20. (Previously presented) A nitride based semiconductor light-emitting device according to Claim 14, wherein said large protrusions are wider in width than the small protrusions.

21-32. (Canceled)